

# PJL9801

## 30V P-Channel Enhancement Mode MOSFET

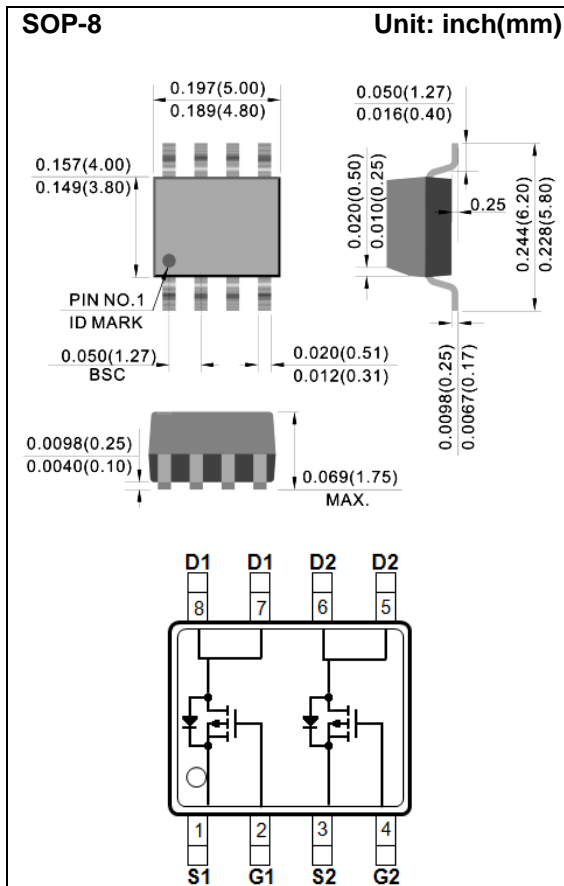
<b>Voltage</b>	<b>-30 V</b>	<b>Current</b>	<b>-5A</b>
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### Features

- $R_{DS(ON)}$  ,  $V_{GS}@-10V$ ,  $I_D@-5.0A<54m\Omega$
- $R_{DS(ON)}$  ,  $V_{GS}@-4.5V$ ,  $I_D@-3.5A<61m\Omega$
- $R_{DS(ON)}$  ,  $V_{GS}@-2.5V$ ,  $I_D@-2.5A<82m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

### Mechanical Data

- Case: SOP-8 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams
- Marking: L9801



## Maximum Ratings and Thermal Characteristics ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	±12	V
Continuous Drain Current		I <sub>D</sub>	5	A
Pulsed Drain Current		I <sub>DM</sub>	20	A
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	2	W
	Derate above 25°C		16	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance		R <sub>θJA</sub>	62.5	°C/W
- Junction to Ambient <sup>(Note 3)</sup>				



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## Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.5	-0.97	-1.3	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.0A	-	45	54	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A	-	51	61	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.5A	-	67	82	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-0.01	-1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	±10	±100	nA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.0A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	9.1	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.8	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	2.6	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	816	-	pF
Output Capacitance	C <sub>oss</sub>		-	64	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	42	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-5.0A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω <sup>(Note 1,2)</sup>	-	5	-	ns
Turn-On Rise Time	tr		-	45	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	66	-	
Turn-Off Fall Time	tf		-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>s</sub>	---	-	-	-2	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	0.77	-1.2	V

### NOTES :

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper
5. Guaranteed by design, not subject to production testing

# PJL9801

## TYPICAL CHARACTERISTIC CURVES

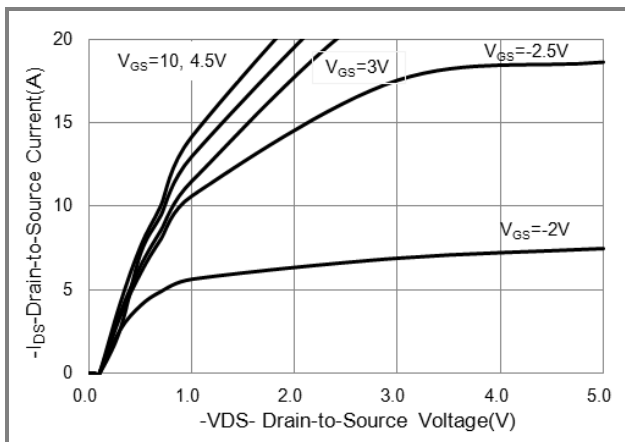


Fig.1 On-Region Characteristics

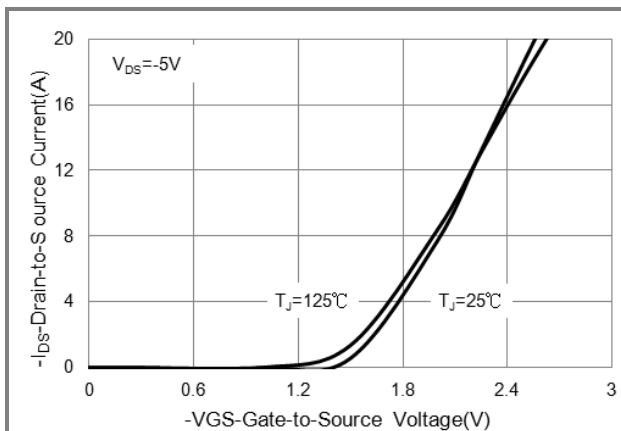


Fig.2 Transfer Characteristics

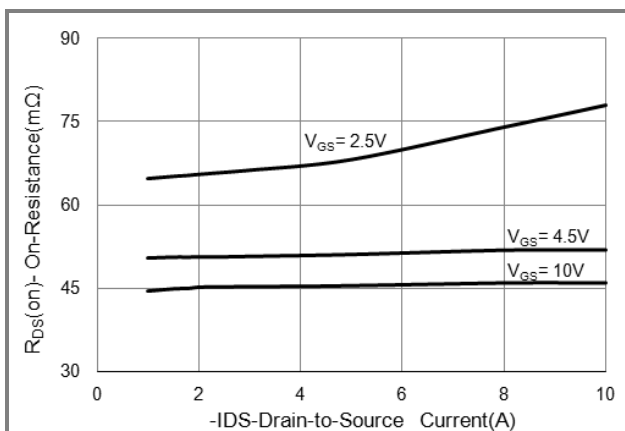


Fig.3 On-Resistance vs. Drain Current

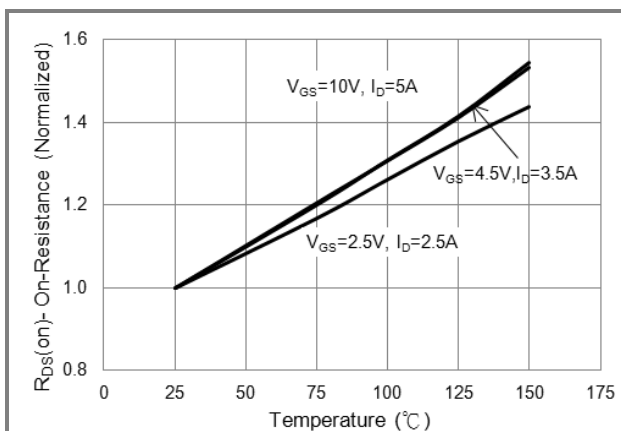


Fig.4 On-Resistance vs. Junction temperature

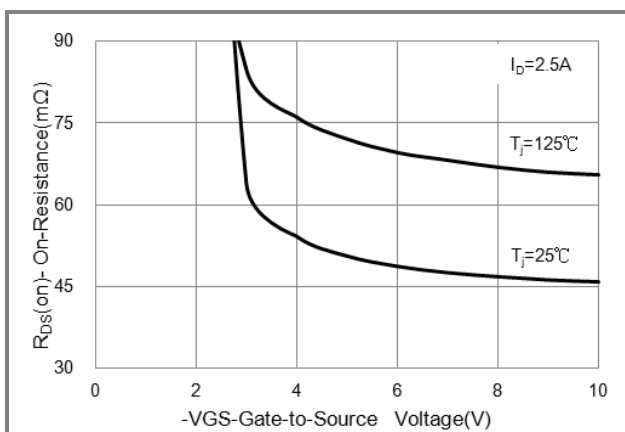


Fig.5 On-Resistance Variation with VGS.

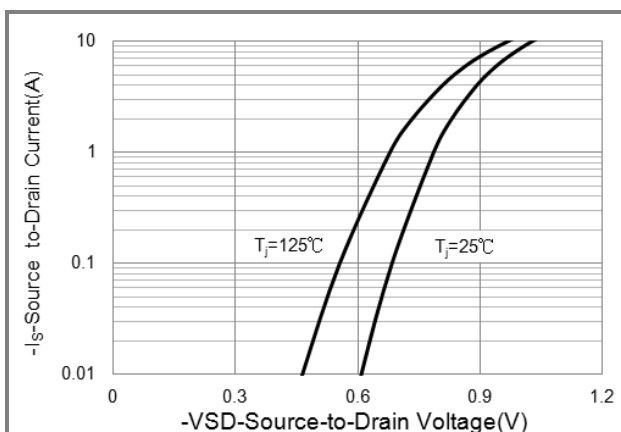


Fig.6 Body Diode Characteristics



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## TYPICAL CHARACTERISTIC CURVES

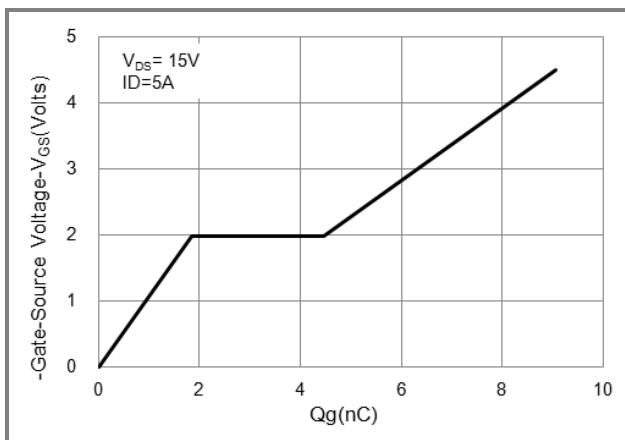


Fig.7 Gate-Charge Characteristics

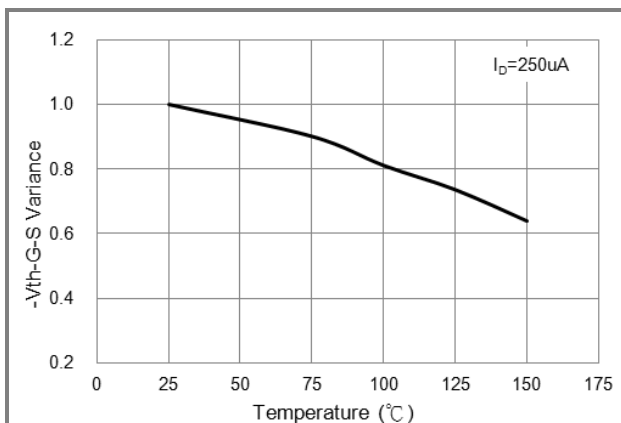


Fig.8 Threshold Voltage Variation with Temperature.

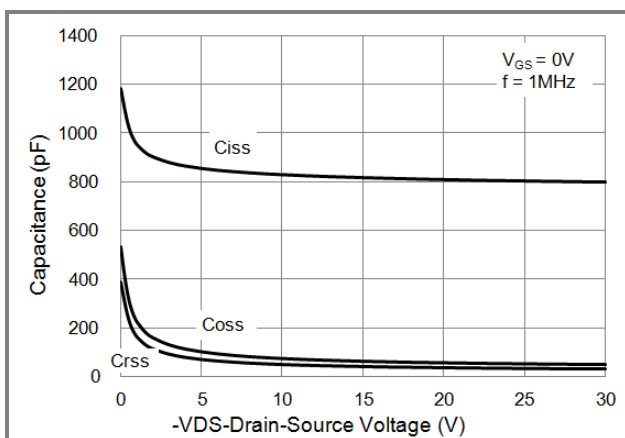


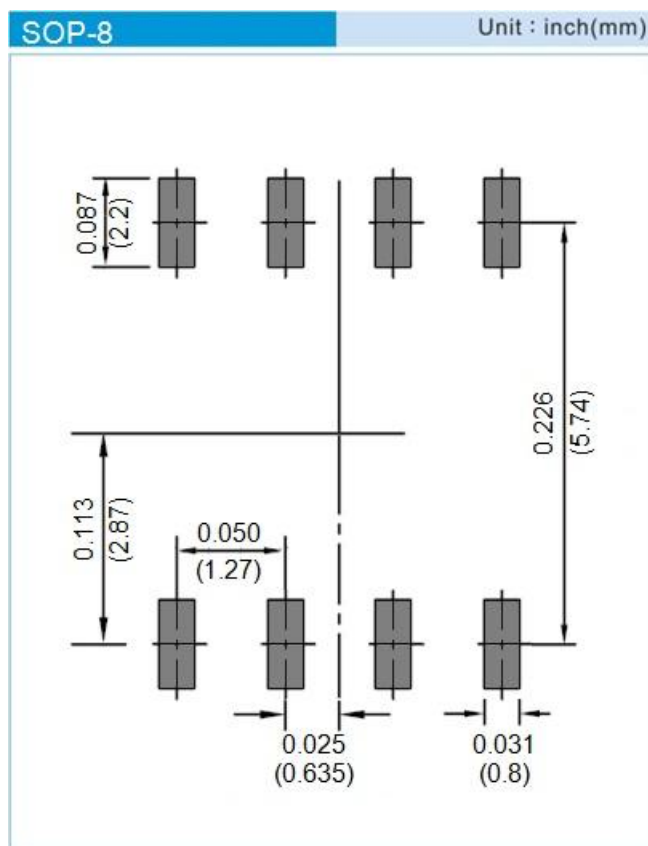
Fig.9 Capacitance vs. Drain-Source Voltage.

# PJL9801

## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJL9801_R2_00001	SOP-8	2.5K pcs / 13" reel	L9801	Halogen free

## MOUNTING PAD LAYOUT





## PJL9801

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